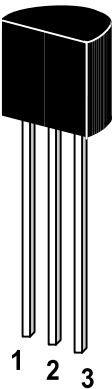


ST 2SC5345

NPN Silicon Epitaxial Planar Transistor
RF amplifier applications.

The transistor is subdivided into three groups, R, O and Y. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



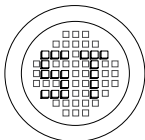
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	20	V
Emitter Base Voltage	V _{EBO}	4	V
Collector Current	I _C	20	mA
Collector Dissipation	P _{tot}	500	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-55 to +150	°C

G S P FORM A IS AVAILABLE



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РАДИОТЕХ

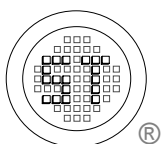
Тел.: (495) 795-0805
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Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SC5345

Characteristics at $T_{amb}=25^{\circ}C$

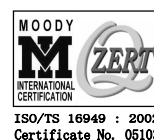
		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=6V$, $I_C=1mA$	R	h_{FE}	40	-	80	-
	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
Collector Base Breakdown Voltage at $I_C=10\mu A$		V_{CBO}	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C=5mA$		V_{CEO}	20	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu A$		V_{EBO}	4	-	-	V
Collector Cutoff Current at $V_{CB}=30V$		I_{CBO}	-	-	0.5	μA
Emitter Cutoff Current at $V_{EB}=4V$		I_{EBO}	-	-	0.5	μA
Collector Emitter Saturation Voltage at $I_C=10mA$, $I_B=1mA$		$V_{CE(sat)}$	-	-	0.3	V
Transition Frequency at $V_{CE}=6V$, $I_E=-1mA$		f_T	-	550	-	MHz
Collector Output Capacitance at $V_{CB}=6V$, $f=1MHz$		C_{OB}	-	1.4	-	pF

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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, acompany
listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 30/03/2004